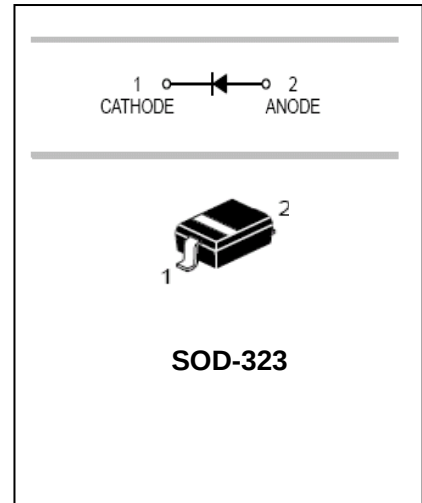


**Silicon Epitaxial Planar Diode****1SS355****FEATURES**

- Small Surface Mounting Type:  
SOD-323
- High Speed : $t_f=1.2\text{ns}$  Typ.
- High Reliability With High Surge Current Handling Capability.



Lead-free

**APPLICATIONS**

- High speed switching

**ORDERING INFORMATION**

| Type No. | Marking | Package Code |
|----------|---------|--------------|
| 1SS355   | A       | SOD-323      |

**MAXIMUM RATING @  $T_a=25^\circ\text{C}$  unless otherwise specified**

| Parameter                           | Symbol      | Limits   | Unit             |
|-------------------------------------|-------------|----------|------------------|
| Non-Repetitive Peak reverse voltage | $V_{RM}$    | 90       | V                |
| DC Reverse Voltage                  | $V_R$       | 80       | V                |
| Peak forward Current                | $I_{FM}$    | 225      | mA               |
| Average Rectified Output Current    | $I_O$       | 100      | mA               |
| Surge current (1s)                  | $I_{surge}$ | 500      | mA               |
| Junction temperature                | $T_j$       | 125      | $^\circ\text{C}$ |
| Storage temperature                 | $T_{STG}$   | -55~+125 | $^\circ\text{C}$ |

## Silicon Epitaxial Planar Diode

**1SS355**

### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

| Parameter                     | Symbol   | Min. | Typ. | Max. | Unit          | Conditions                                      |
|-------------------------------|----------|------|------|------|---------------|-------------------------------------------------|
| Forward voltage               | $V_F$    |      |      | 1.2  | V             | $I_F=100\text{mA}$                              |
| Reverse current               | $I_R$    |      |      | 0.1  | $\mu\text{A}$ | $V_R=80\text{V}$                                |
| Capacitance between terminals | $C_T$    |      |      | 3    | pF            | $V_R=0.5\text{V}, f=1\text{MHz}$                |
| Reverse Recovery Time         | $t_{rr}$ |      |      | 4    | ns            | $I_F=10\text{mA}, V_R=6\text{V}, R_L=100\Omega$ |

### TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

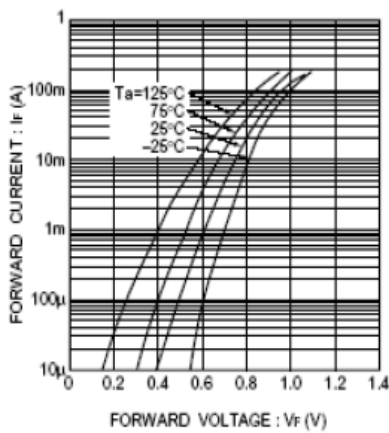


Fig.1 Forward characteristics

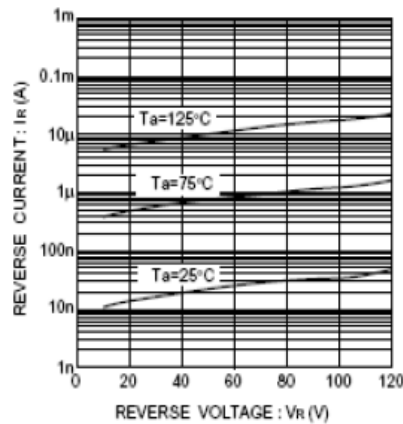


Fig.2 Reverse characteristics

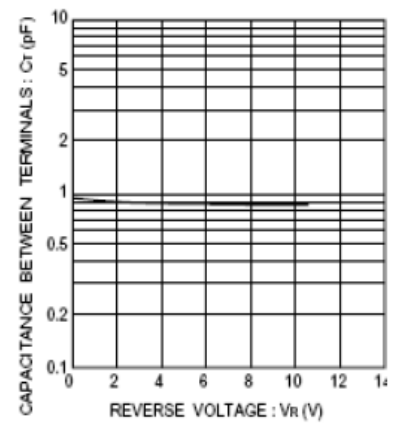


Fig.3 Capacitance between terminals characteristics

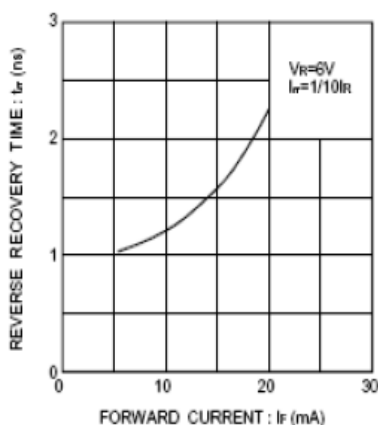


Fig.4 Reverse recovery time characteristics

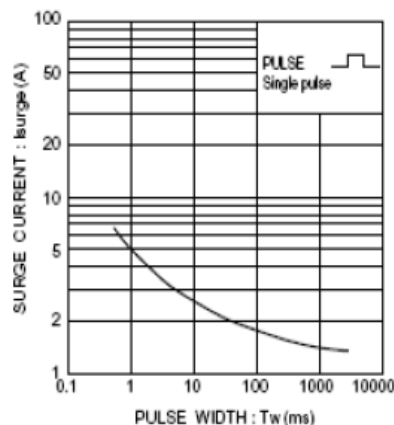


Fig.5 Surge current characteristics

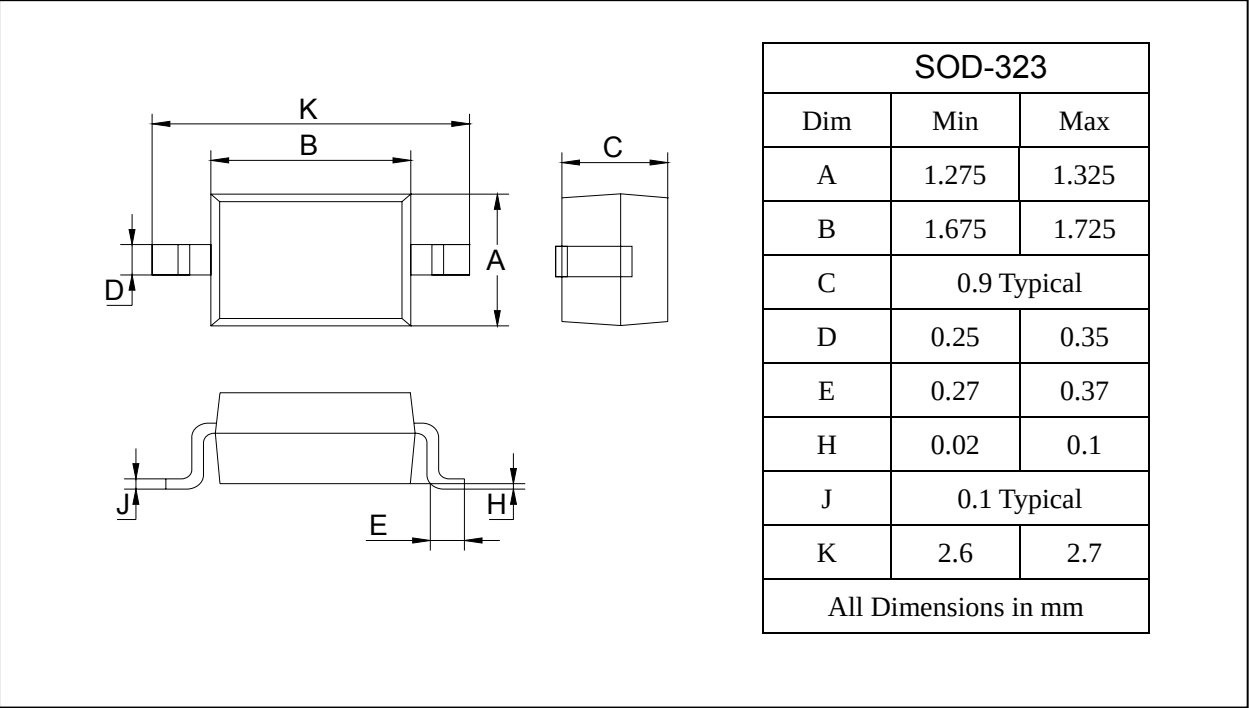
Silicon Epitaxial Planar Diode

1SS355

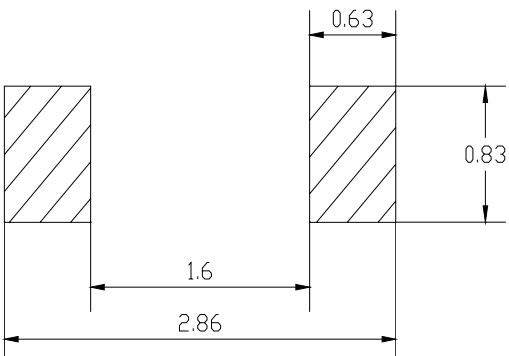
PACKAGE OUTLINE

Plastic surface mounted package

SOD-323



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

| Device | Package | Shipping       |
|--------|---------|----------------|
| 1SS355 | SOD-323 | 3000/Tape&Reel |